Quad 2-input NAND Schmitt trigger Rev. 3 — 30 August 2012

Product data sheet

1. **General description**

The 74HC132; 74HCT132 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A

The 74HC132; 74HCT132 is a quad 2-input NAND gate with Schmitt trigger inputs. This device features reduced input threshold levels to allow interfacing to TTL logic levels. Inputs also include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}. Schmitt trigger inputs transform slowly changing input signals into sharply defined jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H.

Features and benefits 2.

- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

Applications 3.

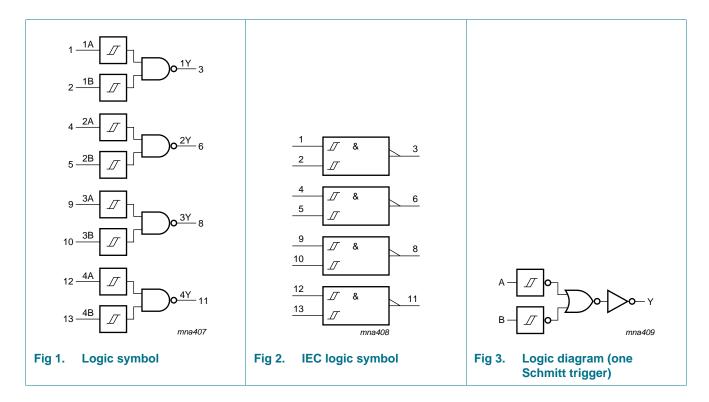
- Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators



4. Ordering information

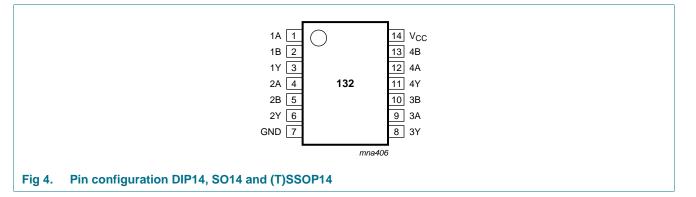
Type number	Package			
	Temperature range	Name	Description	Version
74HC132N	4HC132N -40 °C to +125 °C		plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HCT132N				
74HC132D	HC132D -40 °C to +125 °C		plastic small outline package; 14 leads; body width	SOT108-
74HCT132D			3.9 mm	
74HC132DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-
74HCT132DB			width 5.3 mm	
74HC132PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-
74HCT132PW			body width 4.4 mm	

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
1A to 4A	1, 4, 9, 12	data input
1B to 4B	2, 5, 10, 13	data input
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

7. Functional description

Table 3.Function table

Input		Output
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

	_				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{\rm I}$ < –0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	V_{O} < –0.5 V or V_{O} > V_{CC} + 0.5 V	<u>[1]</u> _	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}}$ + 0.5 V	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[2]		
	DIP14 package		-	750	mW
	SO14, and (T)SSOP14 packages		-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For DIP14 package: P_{tot} derates linearly with 12 mW/K above 70 °C.
 For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For (T)SSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Conditions 74HC132		74HCT132			Unit	
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC13	2									
V _{он}	HIGH-level	$V_I = V_{T+} \text{ or } V_{T-}$								
	output voltage	I_{O} = –20 $\mu A;~V_{CC}$ = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_{O} = –20 $\mu A;~V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{T+} \text{ or } V_{T-}$								
	output voltage	$I_0 = 20 \ \mu A; V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
СС	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	2.0	-	20	-	40	μA
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT1	32									
V _{он}	HIGH-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_I = V_{T+}$ or V_{T-} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA;	-	0	0.1	-	0.1	-	0.1	V
		l _O = 4.0 mA;	-	0.15	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	2.0	-	20	-	40	μA
∆l _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	30	108	-	135	-	147	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; $C_L = 50$ pF; for load circuit see <u>Figure 6</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C to	o +125 °C	Unit
				Min	Тур	Max	Мах (85 °С)	Max (125 °C)	
74HC132	2		1						
t _{pd}	propagation delay	nA, nB to nY; see <u>Figure 5</u>	<u>[1]</u>						
		$V_{CC} = 2.0 V$		-	36	125	155	190	ns
		$V_{CC} = 4.5 V$		-	13	25	31	38	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	11	-	-	-	ns
		$V_{CC} = 6.0 V$		-	10	21	26	32	ns
t _t	transition time	see <u>Figure 5</u>	[2]						
		$V_{CC} = 2.0 V$		-	19	75	95	110	ns
		$V_{CC} = 4.5 V$		-	7	15	19	22	ns
		$V_{CC} = 6.0 V$		-	6	13	16	19	ns
C _{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	<u>[3]</u>	-	24	-	-	-	pF
74HCT1:	32								
t _{pd}	propagation delay	nA, nB to nY; see <u>Figure 5</u>	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	20	33	41	50	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	17	-	-	-	ns
t _t	transition time	$V_{CC} = 4.5 \text{ V}; \text{ see } \frac{\text{Figure 5}}{1000}$	[2]	-	7	15	19	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	<u>[3]</u>	-	20	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

[2] t_t is the same as t_{THL} and t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

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12. Waveforms

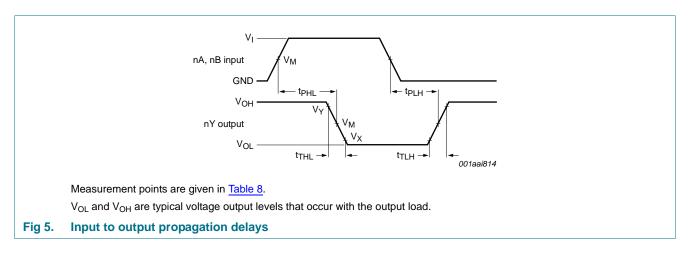
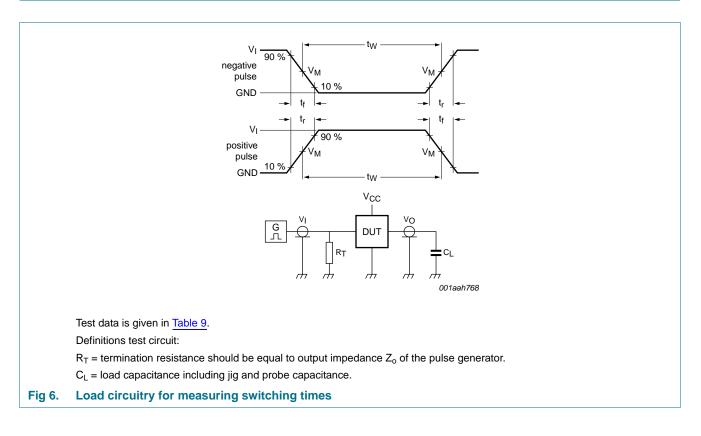


Table 8. **Measurement points**

Туре	Input	Output				
	V _M	V _M	V _X	V _Y		
74HC132	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}		
74HCT132	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}		



74HC132; 74HCT132

Quad 2-input NAND Schmitt trigger

Table 9. Test data				
Туре	Input		Load	Test
	VI	t _r , t _f	CL	
74HC132	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT132	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

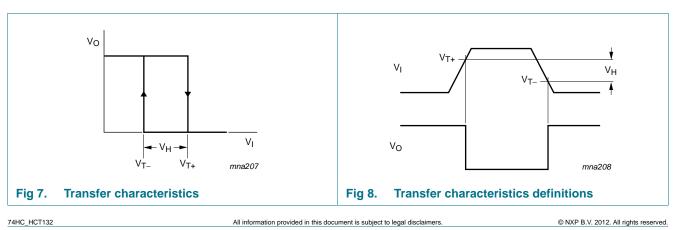
13. Transfer characteristics

Table 10. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); see <u>Figure 7</u> and <u>Figure 8</u>.

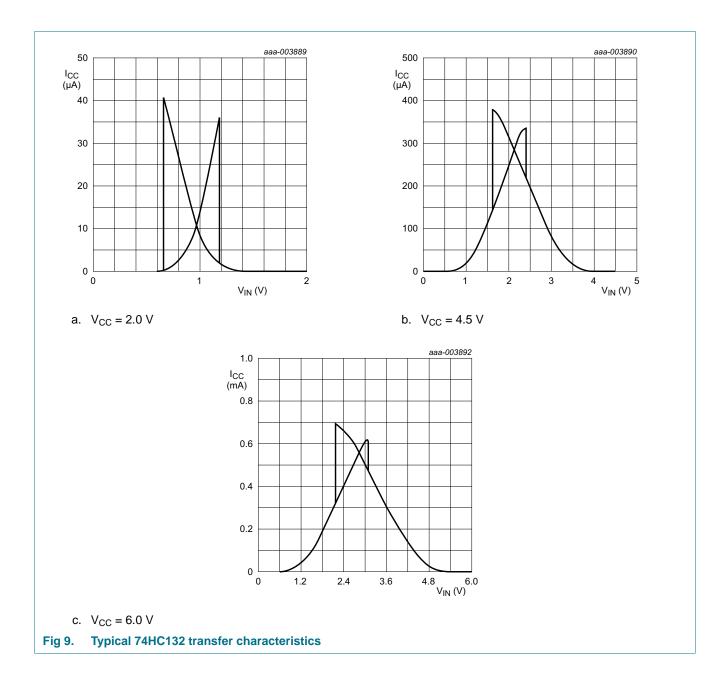
Symbol	Parameter	Conditions		T _{amb} = 25 °C		T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C		Unit
		Min	Тур	Max	Min	Max	Min	Max		
74HC13	2						I			
V _{T+}	positive-going	V _{CC} = 2.0 V	0.7	1.18	1.5	0.7	1.5	0.7	1.5	V
	threshold	$V_{CC} = 4.5 V$	1.7	2.38	3.15	1.7	3.15	1.7	3.15	V
	voltage	$V_{CC} = 6.0 V$	2.1	3.14	4.2	2.1	4.2	2.1	4.2	V
V_{T-}	negative-going	$V_{CC} = 2.0 V$	0.3	0.63	1.0	0.3	1.0	0.3	1.0	V
	threshold	$V_{CC} = 4.5 V$	0.9	1.67	2.2	0.9	2.2	0.9	2.2	V
	voltage	$V_{CC} = 6.0 V$	1.2	2.26	3.0	1.2	3.0	1.2	3.0	V
V _H	hysteresis	$V_{CC} = 2.0 V$	0.2	0.55	1.0	0.2	1.0	0.2	1.0	V
	voltage	$V_{CC} = 4.5 V$	0.4	0.71	1.4	0.4	1.4	0.4	1.4	V
		$V_{CC} = 6.0 V$	0.6	0.88	1.6	0.6	1.6	0.6	1.6	V
74HCT1	32									
V _{T+}	positive-going	$V_{CC} = 4.5 V$	1.2	1.41	1.9	1.2	1.9	1.2	1.9	V
	threshold voltage	$V_{CC} = 5.5 V$	1.4	1.59	2.1	1.4	2.1	1.4	2.1	V
V_{T-}	negative-going	$V_{CC} = 4.5 V$	0.5	0.85	1.2	0.5	1.2	0.5	1.2	V
	threshold voltage	$V_{CC} = 5.5 V$	0.6	0.99	1.4	0.6	1.4	0.6	1.4	V
V _H	hysteresis	$V_{CC} = 4.5 V$	0.4	0.56	-	0.4	-	0.4	-	V
	voltage	V _{CC} = 5.5 V	0.4	0.60	-	0.4	-	0.4	-	V

14. Transfer characteristics waveforms



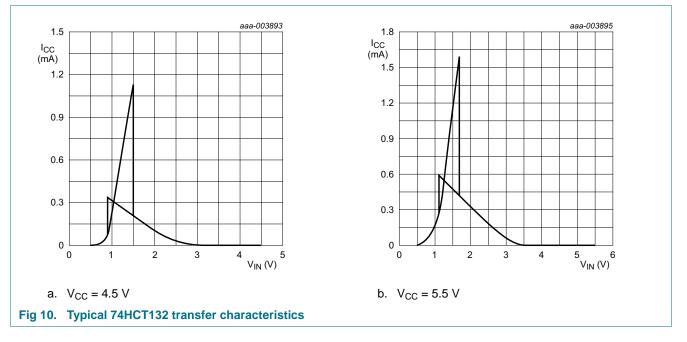
74HC132; 74HCT132

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74HC132; 74HCT132

Quad 2-input NAND Schmitt trigger



15. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC}$ where:

 P_{add} = additional power dissipation (μ W);

 $f_i = input frequency (MHz);$

 t_r = rise time (ns); 10 % to 90 %;

t_f = fall time (ns); 90 % to 10 %;

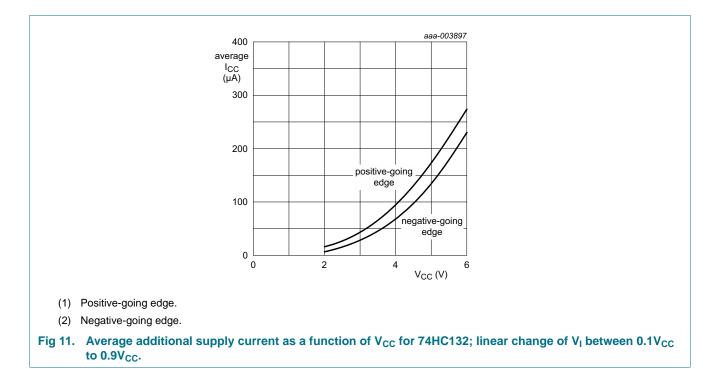
 $\Delta I_{CC(AV)}$ = average additional supply current (µA).

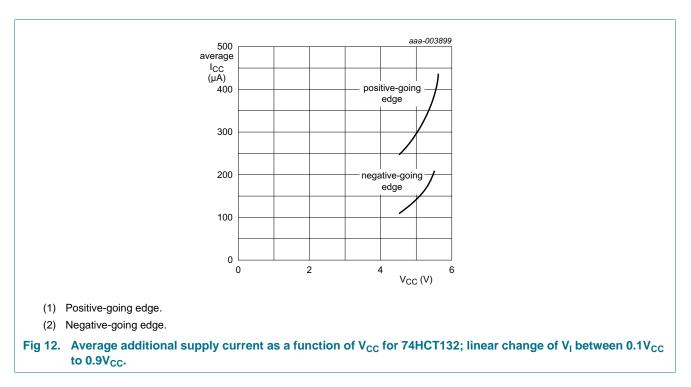
Average $\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in Figure 11 and Figure 12.

An example of a relaxation circuit using the 74HC132; 74HCT132 is shown in Figure 13.

74HC132; 74HCT132

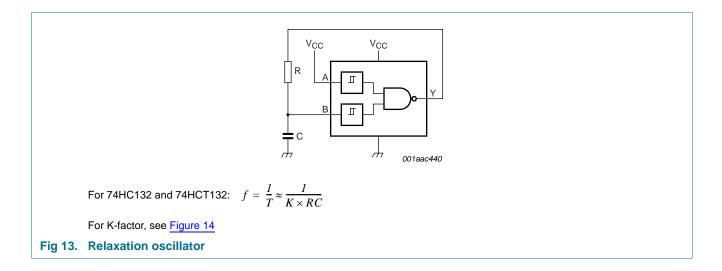
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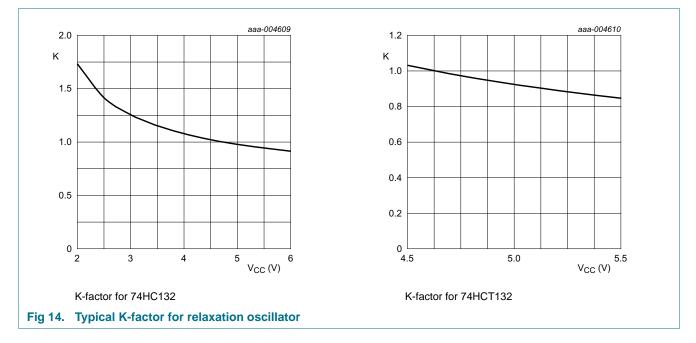




74HC132; 74HCT132

Quad 2-input NAND Schmitt trigger





Quad 2-input NAND Schmitt trigger

16. Package outline

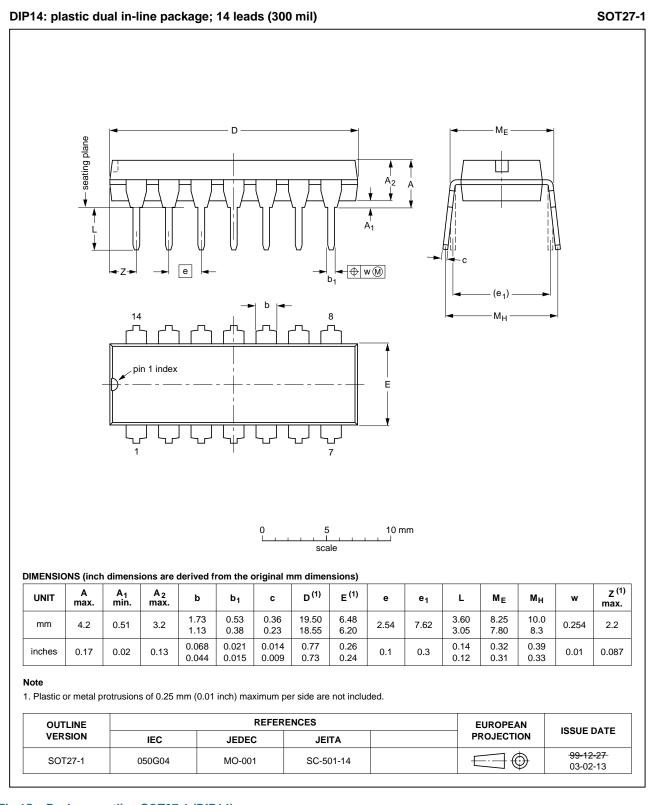


Fig 15. Package outline SOT27-1 (DIP14)

Quad 2-input NAND Schmitt trigger

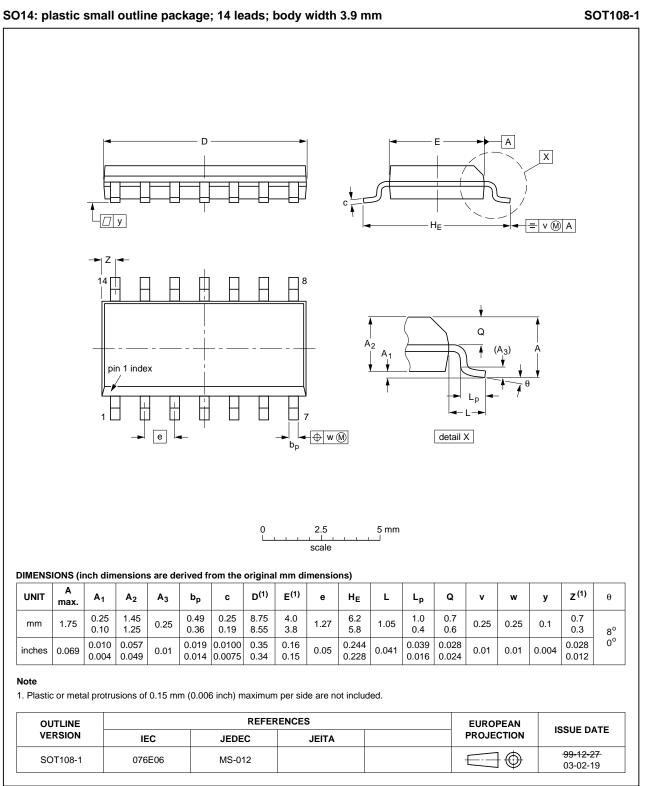


Fig 16. Package outline SOT108-1 (SO14)

Quad 2-input NAND Schmitt trigger

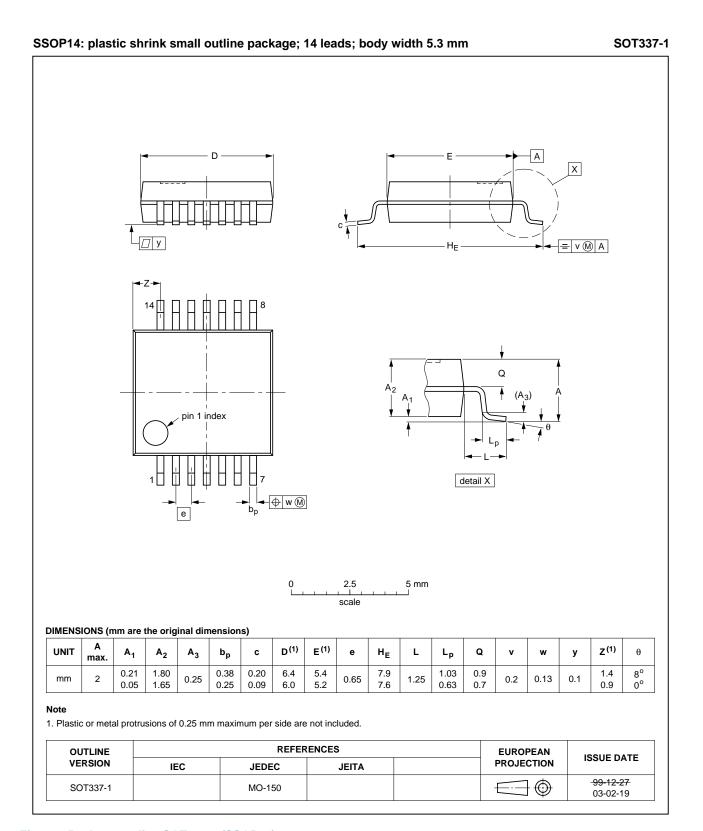


Fig 17. Package outline SOT337-1 (SSOP14)

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Quad 2-input NAND Schmitt trigger

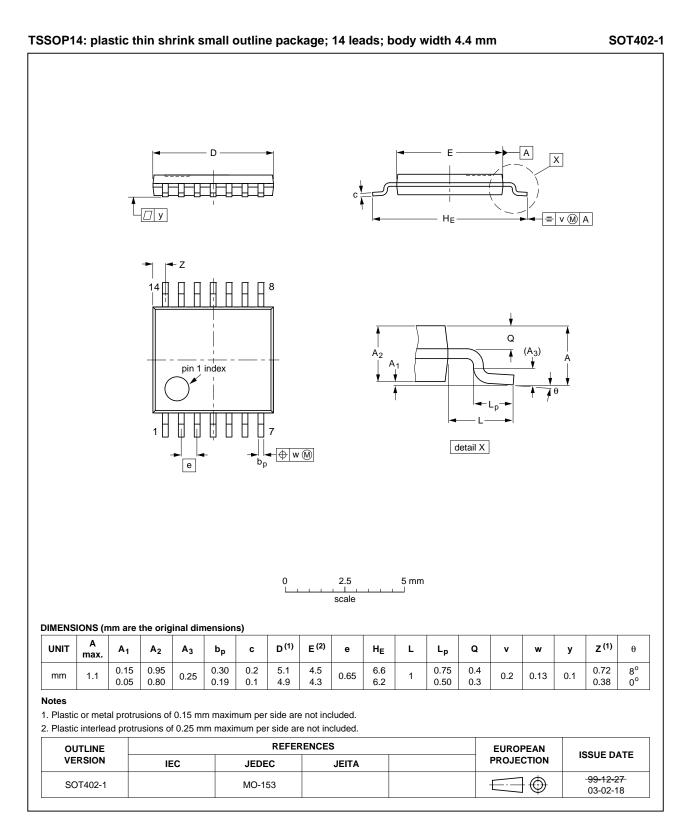


Fig 18. Package outline SOT402-1 (TSSOP14)

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17. Abbreviations

Description Complementary Metal-Oxide Semiconductor
Complementary Metal-Oxide Semiconductor
Device Under Test
ElectroStatic Discharge
Human Body Model
Low-power Schottky Transistor-Transistor Logic
Machine Model
Transistor-Transistor Logic

18. Revision history

Table 12. Revision hist	ory						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
74HC_HCT132 v.3	20120830	Product data sheet	-	74HC_HCT132_CNV v.2			
Modifications:	Modifications: • The format of this data sheet has been redesigned to comply with the new identity guidelin of NXP Semiconductors.						
	 Legal texts have be 	en adapted to the new co	mpany name where	appropriate.			
	 Figure 14 added (ty 	pical K-factor for relaxation	on oscillator).				
74HC_HCT132_CNV v.2	19970826	Product specification	-	-			

19. Legal information

19.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Quad 2-input NAND Schmitt trigger

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Date of release: 30 August 2012 Document identifier: 74HC_HCT132